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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: : GROUP ART UNIT: 2815
JAMAL RAMDANI ET AL :
SERIAL NO.: 09/766,046 : EXAMINER: BAUMEISTER
FILED: JANUARY 19, 2001 :
FOR: STRUCTURE AND METHOD FOR FABRICATING GAN DEVICES UTILIZING THE
FORMATION OF A COMPLIANT SUBSTRATE

RESPONSE TO THE OFFICE COMMUNICATION DATED JANUARY 3, 2003

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action dated January 3, 2003, please amend the claims as follows.

IN THE CLAIMS

Please amend Claim 7, 8, 10, 11, 13, 14, and 15 as follows.

--7. (Amended) The semiconductor structure of claim 6, wherein the template layer is formed of material selected from the group comprising Ti-As, Sr-O-As, Sr-Ga-O, Ti-O-As or Sr-Al-O.

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8. (Amended) The semiconductor structure of claim 6, wherein the template layer comprises a Zintl-type phase material.

10. (Amended) The semiconductor structure of claim 6, wherein the template layer comprises a surfactant material.